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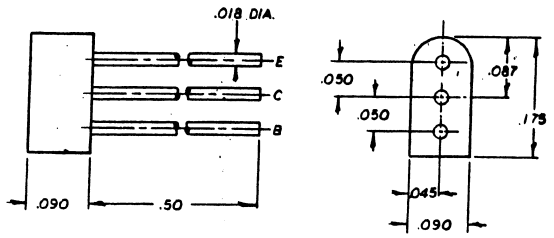
2N4291

Silicon PNP Transistor GEM

APPLICATIONS

This transistor is designed for small signal general purpose applications where the low leakage currents and inherent stability of silicon devices are required.

MECHANICAL OUTLINE



MAXIMUM RATINGS

Total Device Dissipation - 25°C Free Air	**250mW**
Operating and/or Storage Temperature	**−55 to +150°C**

DESIGN CHARACTERISTICS AT 25°C (Except as Noted)

SYMBOL	PARAMETER	TEST CONDITIONS	MIN.	MAX.	UNITS
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\mu A$, $I_E = 0$	−40	-	V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10mA$, $I_B = 0$	−30	-	V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100\mu A$, $I_C = 0$	−6	-	V
I_{CBO}	Collector Leakage Current	$V_{CB} = -15V$	-	0.2	μA
h_{FE}	Forward Current Transfer Ratio	$V_{CE} = -10V$, $I_C = 0.1mA$	30	-	-
		$I_C = 10mA$	50	-	-
		$I_C = 100mA$	100	300	-
$V_{CE(sat)}$	Collector Saturation Voltage	$I_C = 100mA$, $I_B = 10mA$	-	−0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 100mA$, $I_B = 10mA$	-	−1.5	V
C_{ob}	Output Capacitance	$V_{CB} = -10V$, $f = 140kc$	-	10	pf
h_{fe}	High Frequency Current Gain	$I_C = 10mA$, $V_{CE} = -10V$, $f = 100mc$	1.0	-	-

Quality Semi-Conductors